

# Contents

<b>Abstract</b>	<b>i</b>
<b>Zusammenfassung</b>	<b>iii</b>
<b>Acknowledgements</b>	<b>v</b>
<b>List of Symbols</b>	<b>vii</b>
<b>List of Abbreviations</b>	<b>ix</b>
<b>List of Figures</b>	<b>xv</b>
<b>List of Tables</b>	<b>xix</b>
<b>1 Introduction</b>	<b>1</b>
1.1 Material synthesis and properties of $\text{Bi}_2\text{Se}_3$ . . . . .	4
1.1.1 Thermoelectric and thermoresistive properties . . . . .	5
1.1.2 Memristive properties . . . . .	8
1.1.3 $\text{Bi}_2\text{Se}_3$ . . . . .	9
1.2 Research objectives . . . . .	12
1.3 Thesis overview . . . . .	14
<b>2 <math>\text{Bi}_2\text{Se}_3</math>: electrodeposition and material characterization</b>	<b>15</b>
2.1 Introduction & motivation . . . . .	15
2.2 Experimental . . . . .	15
2.2.1 Electrodeposition . . . . .	15
2.2.2 Design and fabrication of templates . . . . .	17
2.2.3 Characterization . . . . .	20
2.2.3.1 Structural properties . . . . .	20
2.2.3.2 Electrical, thermal and thermoelectric char- acterization . . . . .	23

2.3	Results . . . . .	28
2.3.1	Electrodeposition studies . . . . .	28
2.3.1.1	Electrolyte concentrations . . . . .	28
2.3.1.2	Effect of KCl . . . . .	30
2.3.1.3	Influence of pulsed plating . . . . .	33
2.3.2	Structural properties . . . . .	35
2.3.2.1	Cross-sectional morphology and stoichiometry	35
2.3.2.2	Analysis of the crystal structure . . . . .	37
2.3.3	Electronic properties . . . . .	40
2.3.3.1	Thermoelectric properties . . . . .	40
2.3.3.2	Electrical and thermoresistive properties . . .	42
2.3.3.3	Thermal properties . . . . .	48
2.4	Chapter summary . . . . .	50
<b>3</b>	<b>Bi<sub>2</sub>Se<sub>3</sub> thermoelectric &amp; thermoresistive devices: design, fabrication &amp; characterization</b>	<b>53</b>
3.1	Introduction & motivation . . . . .	53
3.2	Sensor design considerations . . . . .	53
3.2.1	Choice of substrate . . . . .	53
3.2.2	Choice of matrix material . . . . .	54
3.2.3	Bottom contacts . . . . .	54
3.2.4	n-type and p-type . . . . .	56
3.2.4.1	Electrodeposition of copper . . . . .	57
3.2.4.2	Electrical characterization of copper . . . . .	57
3.2.5	Selective electroplating . . . . .	59
3.2.6	Top contacts . . . . .	59
3.3	Demonstration of process flow . . . . .	60
3.3.1	Bottom contact structuring . . . . .	60
3.3.2	Oxide structuring . . . . .	61
3.3.3	SU-8 processing . . . . .	61
3.3.4	Bi <sub>2</sub> Se <sub>3</sub> plating . . . . .	62
3.3.5	Planarization . . . . .	62
3.3.6	Temporary photoresist & oxide removal . . . . .	62
3.3.7	Copper plating & planarization . . . . .	64
3.3.8	Temporary photoresist & oxide/metal removal . . . . .	64
3.3.9	Top contact evaporation . . . . .	64

3.4	Sensor characterization . . . . .	64
3.4.1	Sensor performance . . . . .	66
3.4.1.1	Temperature sensitivity . . . . .	66
3.4.1.2	Heatflux sensitivity . . . . .	69
3.4.1.3	Temperature accuracy . . . . .	70
3.4.1.4	Heatflux accuracy . . . . .	73
3.4.1.5	Resolution . . . . .	73
3.5	Chapter summary . . . . .	75
<b>4</b>	<b>Bi<sub>2</sub>Se<sub>3</sub> based sensor systems: integration aspects</b>	<b>77</b>
4.1	Introduction and motivation . . . . .	77
4.1.1	Energy harvester . . . . .	78
4.1.2	Dual-mode sensor . . . . .	79
4.1.3	Sense-log device . . . . .	80
4.2	Bi <sub>2</sub> Se <sub>3</sub> memristors: fabrication . . . . .	81
4.2.1	Top contact . . . . .	82
4.2.2	Implication for integration . . . . .	84
4.3	Bi <sub>2</sub> Se <sub>3</sub> memristors: characterization framework . . . . .	85
4.3.1	Framework theory . . . . .	86
4.3.2	Framework application . . . . .	88
4.3.2.1	IV & RV characteristics . . . . .	88
4.3.2.2	WE-measurements . . . . .	90
4.3.2.3	WRER-measurements . . . . .	92
4.3.2.4	Conclusion on the framework . . . . .	95
4.4	Bi <sub>2</sub> Se <sub>3</sub> sense-log systems . . . . .	96
4.4.1	Bi <sub>2</sub> Se <sub>3</sub> modelling . . . . .	96
4.4.2	Bi <sub>2</sub> Se <sub>3</sub> measurements . . . . .	99
4.5	Low resistance TEG sense-log systems . . . . .	102
4.6	Discussion and sense-log opportunities . . . . .	108
4.6.0.1	Sensing complexity . . . . .	109
4.6.0.2	Directionality . . . . .	109
4.6.0.3	Reversibility . . . . .	109
4.6.0.4	Heatflux sensing capability . . . . .	110
4.6.0.5	Temperature sensing capability . . . . .	110
4.7	Chapter summary . . . . .	110
<b>5</b>	<b>Conclusion</b>	<b>113</b>

<b>6 Outlook</b>	<b>115</b>
6.1 n-type legs . . . . .	115
6.2 Memristor tuning . . . . .	115
6.3 Indirect probing & device integration . . . . .	116
<b>A Appendix A - Error propagation</b>	<b>117</b>
A.1 General gaussian formula for error propagation . . . . .	117
A.2 Simplification for case of multiplication by a constant . . . . .	117
A.3 Simplification for case of addition and subtraction . . . . .	117
A.4 Simplification for case of multiplication and division . . . . .	118
<b>B Appendix B - Electrochemistry and characterization</b>	<b>119</b>
B.1 Thermoelectric setup . . . . .	119
B.2 Deposition regime . . . . .	120
B.3 Determination of the faraday efficiency . . . . .	122
B.4 Chemical diagrams from medusa . . . . .	122
B.5 Raman and XRD measurements . . . . .	124
<b>C Appendix C - Device processing</b>	<b>127</b>
C.1 Electrochemical experiments . . . . .	127
C.2 Electrolyte mixing . . . . .	127
C.3 Electrochemical deposition of thermoelectric pillars . . . . .	128
C.4 TEG pillar processing . . . . .	128
C.5 TEG chain processing . . . . .	129
C.6 Top contact of thermoelectric pillars and devices . . . . .	132
C.7 Electrochemical deposition of memristors . . . . .	133
C.8 Top contact of memristors . . . . .	133
C.9 Processing comparison of TEGs and memristors . . . . .	134
C.10 Electrodeposition experiment with $Sb_2Te_3$ & $Bi_2Te_3$ . . . . .	136
C.11 Thermal computations . . . . .	138
<b>D Appendix D - Thermoelectric thermoresistive device B</b>	<b>141</b>
<b>E Appendix E - List of samples</b>	<b>143</b>
<b>Bibliography</b>	<b>149</b>
<b>Publications</b>	<b>167</b>
<b>Curriculum Vitae</b>	<b>169</b>